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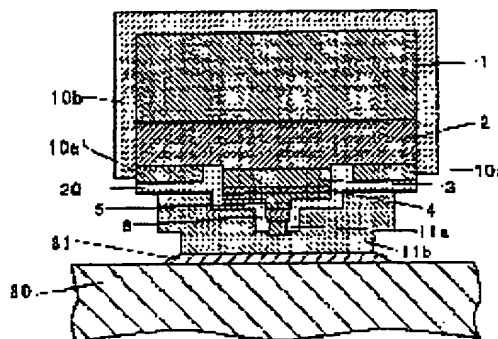
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(54) NITRIDE SEMICONDUCTOR DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To reduce the contact resistance between a substrate and either an n-electrode or p-electrode by providing a semiconductor layer and the n- and p-electrodes on the first main surface side of the substrate and a first electrode, continuously from the second major surface and side face of the substrate and connecting the first electrode to either one of the n- and p-electrodes and insulating the electrode from the other electrode by forming an insulating film on the first major surface side.

SOLUTION: On the first major surface side of a substrate 1, an n-type contact layer 2, an n-type clad layer 3, an active layer 4, a p-type clad layer 5, and a contact layer 6 are formed. Over nearly the entire surface of the contact layer 6, a p-type electrode 11a for ohmic contact, and a second electrode 11b which is connected to the electrode 11a are formed and stuck to a supporting body 30 with a conductive adhesive 31. On the second major surface side of the substrate 1, n-electrodes 10a and 10a' are formed, and a first electrode 10b which is connected to the electrodes 10a and 10a' is formed continuously from the second major surface and the side face of the substrate 1. The electrode 10b is insulated from the p-electrode 11a and second electrode 11b by an insulating film 20, formed on the first major surface of the substrate 1.



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